

Phase selective growth of rhombohedral MoS₂ for optoelectronic applications

Ramesh Rajarapu^{1, 2}

Prahalad K Barman,^{1, 2} Renu Yadav,^{1, 2} Rabindra Biswas,³ Saroj Poudyal,^{1, 2} Bubunu Biswal,^{1, 2} Varun Raghunathan,³ Pramoda Kumar Nayak,^{1, 2,*} Abhishek Misra^{1, 2,*}

¹Centre for 2D Materials Research and Innovations, Indian Institute of Technology, Madras 600036, India

²Department of Physics, Indian Institute of Technology, Madras 600036, India

³Department of Electrical Communication Engineering, Indian Institution of Science, Bangalore-560012, India

Abhishek.misra@iitm.ac.in, pnyayak@iitm.ac.in

The synthesis of materials with desired polymorphic phases in a chemical vapor deposition (CVD) process necessitates a meticulous balance among various thermodynamic variables. In this study, we present a methodology to synthesize rhombohedral (3R) phase MoS₂ in well-defined sword-like geometry, exhibiting lengths of up to 120 μm , uniform widths ranging from 2-3 μm , and thicknesses of 3-7 nm by precisely controlling the dynamics of carrier gas flow from continuous mode to pulsed mode during the CVD growth process. To validate the formation of the 3R phase material, we investigate its characteristic signatures. The resulting MoS₂ swords exhibit a high degree of circular dichroism ($\sim 58\%$ at 100 K), accompanied by a distinctive evolution of low-frequency Raman peaks and an increasing intensity of second harmonic signals with increasing number of layers.¹ These findings conclusively establish the presence of the 3R phase in the material. Further, a field effect mobility of 40 $\text{cm}^2/\text{V}\cdot\text{s}$ and an $I_{\text{on}}/I_{\text{off}}$ ratio of $\sim 10^6$ confirm the exceptional electronic quality of the 3R-phase MoS₂. These findings hold significant promise for the advancement of emerging quantum electronic devices, valley-based physics and nonlinear optical phenomena in layered materials.

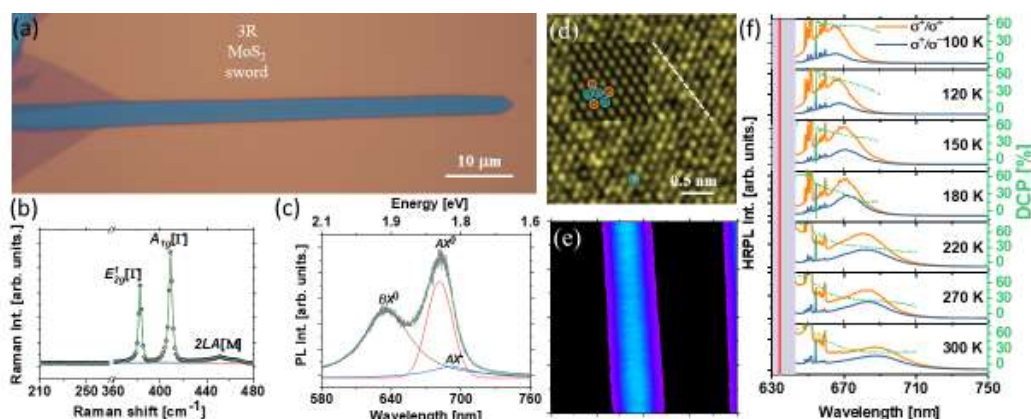


Figure 1. (a) Optical microscope image of 3R-MoS₂ grown on SiO₂/Si (b-c) Single point Raman and PL profiles of MoS₂ (d) High-resolution transmission electron microscopy image of MoS₂ (e-f) Second harmonic generation mapping and helicity resolved photoluminescence of MoS₂

References

- [1] Ramesh R, Barman PK, Yadav R, Biswas R, Devaraj M, Poudyal S, Biswal B, Gupta VL, Pradhan G.K, Raghunathan V, Nayak PK, Misra A. ACS Nano 16, 12, 2022, 21366–21376